

119 and 209 BGA
Commercial Temp36Mb Pipelined and Flow Through
Synchronous NBT SRAM250 MHz–133 MHz
2.5 V or 3.3 V V_DD
2.5 V or 3.3 V I/O

Features

- NBT (No Bus Turn Around) functionality allows zero wait Read-Write-Read bus utilization; fully pin-compatible with both pipelined and flow through NtRAMTM, NoBLTM and ZBTTM SRAMs
- 2.5 V or 3.3 V +10%/-5% core power supply
- 2.5 V or 3.3 V I/O supply
- User-configurable Pipeline and Flow Through mode
- ZQ mode pin for user-selectable high/low output drive
- IEEE 1149.1 JTAG-compatible Boundary Scan
- On-chip write parity checking; even or odd selectable
- On-chip parity encoding and error detection
- LBO pin for Linear or Interleave Burst mode
- Pin-compatible with 2Mb, 4Mb, 8Mb, and 16Mb devices
- Byte write operation (9-bit Bytes)
- 3 chip enable signals for easy depth expansion
- ZZ Pin for automatic power-down
- JEDEC-standard 119- or 209-Bump BGA package

		-250	-225	-200	-166	-150	-133	Unit
Pipeline	t _{KQ}	2.3	2.5	3.0	3.5	3.8	4.0	ns
3-1-1-1	tCycle	4.0	4.4	5.0	6.0	6.6	7.5	ns
	Curr (x18)	365	335	305	265	245	215	mA
3.3 V	Curr (x36)	560	510	460	400	370	330	mΑ
	Curr (x72)	660	600	540	460	430	380	mA
	Curr (x18)	360	330	305	260	240	215	mA
2.5 V	Curr (x36)	550	500	460	390	360	330	mΑ
	Curr (x72)	640	590	530	450	420	370	mA
Flow	t _{KQ}	6.0	6.5	7.5	8.5	10	11	ns
Through 2-1-1-1	tCycle	7.0	7.5	8.5	10	10	15	ns
	Curr (x18)	235	230	210	200	195	150	mA
3.3 V	Curr (x36)	300	300	270	270	270	200	mΑ
	Curr (x72)	350	350	300	300	300	220	mA
	Curr (x18)	235	230	210	200	195	145	mA
2.5 V	Curr (x36)	300	300	270	270	270	190	mΑ
	Curr (x72)	340	340	300	300	300	220	mA

Functional Description

The GS8322Z18/36/72 is a 36Mbit Synchronous Static SRAM. GSI's NBT SRAMs, like ZBT, NtRAM, NoBL or other pipelined read/double late write or flow through read/ single late write SRAMs, allow utilization of all available bus bandwidth by eliminating the need to insert deselect cycles when the device is switched from read to write cycles.

Because it is a synchronous device, address, data inputs, and read/write control inputs are captured on the rising edge of the

input clock. Burst order control ($\overline{\text{LBO}}$) must be tied to a power rail for proper operation. Asynchronous inputs include the Sleep mode enable (ZZ) and Output Enable. Output Enable can be used to override the synchronous control of the output drivers and turn the RAM's output drivers off at any time. Write cycles are internally self-timed and initiated by the rising edge of the clock input. This feature eliminates complex offchip write pulse generation required by asynchronous SRAMs and simplifies input signal timing.

The GS8322Z18/36/72 may be configured by the user to operate in Pipeline or Flow Through mode. Operating as a pipelined synchronous device, in addition to the rising-edge-triggered registers that capture input signals, the device incorporates a rising edge triggered output register. For read cycles, pipelined SRAM output data is temporarily stored by the edge-triggered output register during the access cycle and then released to the output drivers at the next rising edge of clock.

The GS8322Z18/36/72 is implemented with GSI's high performance CMOS technology and is available in a JEDEC-standard 119-bump or 209-bump BGA package.



GS8322Z72B Pad Out 209-Bump BGA—Top View

	1	2	3	4	5	6	7	8	9	10	11	_
А	DQG5	DQ _{G1}	A13	E2	A14	ADV	A15	E3	A17	DQB1	DQB5	А
В	DQG6	DQ _{G2}	BC	BG	NC	W	A16	BB	BF	DQB2	DQB6	В
С	DQG7	DQ _{G3}	BH	BD	NC	E1	NC	BE	BA	DQB3	DQB7	С
D	DQG8	DQG4	V_{SS}	NC	NC	G	NC	NC	V _{SS}	DQB4	DQB8	D
Е	DQP _{G9}	DQPc9	V _{DDQ}	V _{DDQ}	V _{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	DQPF9	DQP _{B9}	E
F	DQC4	DQC8	V_{SS}	V_{SS}	V_{SS}	ZQ	V_{SS}	V _{SS}	V _{SS}	DQF8	DQF4	F
G	DQC3	DQC7	V _{DDQ}	V _{DDQ}	V_{DD}	MCH	V_{DD}	V _{DDQ}	V _{DDQ}	DQF7	DQF3	G
Н	DQc2	DQC6	V_{SS}	V_{SS}	V_{SS}	MCL	V_{SS}	V _{SS}	V _{SS}	DQF6	DQF2	Н
J	DQc1	DQC5	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V_{DD}	V _{DDQ}	V _{DDQ}	DQF5	DQF1	J
К	NC	NC	СК	NC	V_{SS}	MCL	V_{SS}	NC	NC	NC	NC	к
L	DQH1	DQH5	V _{DDQ}	V _{DDQ}	V _{DD}	FT	V _{DD}	V _{DDQ}	V _{DDQ}	DQA5	DQA1	L
М	DQH2	DQH6	V_{SS}	V_{SS}	V_{SS}	MCL	V_{SS}	V _{SS}	V _{SS}	DQA6	DQA2	М
Ν	DQH3	DQH7	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V_{DD}	V _{DDQ}	V _{DDQ}	DQA7	DQA3	Ν
Ρ	DQH4	DQH8	V _{SS}	V_{SS}	V_{SS}	ZZ	V_{SS}	V _{SS}	V _{SS}	DQA8	DQA4	Р
R	DQPD9	DQPH9	V _{DDQ}	V _{DDQ}	V _{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	DQPA9	DQPE9	R
Т	DQD8	DQD4	V _{SS}	NC	NC	LBO	PE	NC	V _{SS}	DQE4	DQE8	Т
U	DQD7	DQD3	NC	A12	NC	A11	A18	A10	NC	DQE3	DQE7	U
V	DQD6	DQD2	A9	A8	A7	A1	A6	A5	A4	DQE2	DQE6	V
W	DQD5	DQD1	TMS	TDI	A3	A0	A2	TDO	ТСК	DQE1	DQE5	W

11 x 19 Bump BGA—14 x 22 mm² Body—1 mm Bump Pitch



GS8322Z36C Pad Out 209-Bump BGA—Top View

	1	2	3	4	5	6	7	8	9	10	11	
А	NC	NC	A13	E2	A14	ADV	A15	E3	A17	DQB1	DQB5	А
В	NC	NC	BC	NC	A19	W	A16	BB	NC	DQB2	DQB6	В
С	NC	NC	NC	BD	NC	E1	NC	NC	BA	DQB3	DQB7	С
D	NC	NC	V_{SS}	NC	NC	G	NC	NC	V _{SS}	DQB4	DQB8	D
Е	NC	DQPc9	V _{DDQ}	V _{DDQ}	V _{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	NC	DQP _{B9}	E
F	DQC4	DQC8	V_{SS}	V_{SS}	V_{SS}	ZQ	V_{SS}	V_{SS}	V_{SS}	NC	NC	F
G	DQC3	DQC7	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V _{DD}	V _{DDQ}	V _{DDQ}	NC	NC	G
Н	DQc2	DQC6	V_{SS}	V_{SS}	V_{SS}	MCL	V_{SS}	V _{SS}	V _{SS}	NC	NC	Н
J	DQC1	DQC5	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V _{DD}	V _{DDQ}	V _{DDQ}	NC	NC	J
K	NC	NC	СК	NC	V_{SS}	MCL	V_{SS}	NC	NC	NC	NC	К
L	NC	NC	V _{DDQ}	V _{DDQ}	V _{DD}	FT	V _{DD}	V _{DDQ}	V _{DDQ}	DQA5	DQA1	L
М	NC	NC	V_{SS}	V_{SS}	V_{SS}	MCL	V_{SS}	V _{SS}	V _{SS}	DQA6	DQA2	М
Ν	NC	NC	V _{DDQ}	V _{DDQ}	V_{DD}	MCH	V _{DD}	V _{DDQ}	V _{DDQ}	DQA7	DQA3	Ν
Ρ	NC	NC	V_{SS}	V_{SS}	V_{SS}	ZZ	V_{SS}	V _{SS}	V _{SS}	DQA8	DQA4	Р
R	DQPD9	NC	V _{DDQ}	V _{DDQ}	V_{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	DQPA9	NC	R
Т	DQD8	DQD4	V_{SS}	NC	NC	LBO	PE	NC	V _{SS}	NC	NC	Т
U	DQD7	DQD3	NC	A12	NC	A11	A18	A10	NC	NC	NC	U
V	DQD6	DQD2	A9	A8	A7	A1	A6	A5	A4	NC	NC	V
W	DQD5	DQD1	TMS	TDI	A3	A0	A2	TDO	ТСК	NC	NC	W

11 x 19 Bump BGA—14 x 22 mm² Body—1 mm Bump Pitch



GS8322Z18C Pad Out 209-Bump BGA—Top View

	1	2	3	4	5	6	7	8	9	10	11	
А	NC	NC	A13	E2	A14	ADV	A15	E3	A17	NC	NC	Α
В	NC	NC	BB	NC	A19	W	A16	NC	NC	NC	NC	В
С	NC	NC	NC	NC	NC	E1	A20	NC	BA	NC	NC	С
D	NC	NC	V_{SS}	NC	NC	G	NC	NC	V _{SS}	NC	NC	D
E	NC	<i>DQP</i> в9	V _{DDQ}	V _{DDQ}	V _{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	NC	NC	E
F	DQB4	DQB8	V_{SS}	V_{SS}	V_{SS}	ZQ	V_{SS}	V _{SS}	V_{SS}	NC	NC	F
G	DQB3	DQ _{B7}	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V _{DD}	V _{DDQ}	V _{DDQ}	NC	NC	G
Н	DQB2	DQB6	V _{SS}	V _{SS}	V _{SS}	MCL	V_{SS}	V _{SS}	V_{SS}	NC	NC	Н
J	DQB1	DQ _{B5}	V _{DDQ}	V _{DDQ}	V _{DD}	MCH	V_{DD}	V _{DDQ}	V _{DDQ}	NC	NC	J
К	NC	NC	СК	NC	V _{SS}	MCL	V _{SS}	NC	NC	NC	NC	к
L	NC	NC	V _{DDQ}	V _{DDQ}	V _{DD}	FT	V _{DD}	V _{DDQ}	V _{DDQ}	DQA5	DQA1	L
М	NC	NC	V _{SS}	V _{SS}	V _{SS}	MCL	V _{SS}	V _{SS}	V _{SS}	DQA6	DQA2	М
Ν	NC	NC	V _{DDQ}	V _{DDQ}	V _{DD}	МСН	V _{DD}	V _{DDQ}	V _{DDQ}	DQA7	DQA3	N
Ρ	NC	NC	V _{SS}	V _{SS}	V _{SS}	ZZ	V _{SS}	V _{SS}	V _{SS}	DQA8	DQA4	Р
R	NC	NC	V _{DDQ}	V _{DDQ}	V _{DD}	V _{DD}	V _{DD}	V _{DDQ}	V _{DDQ}	DQPA9	NC	R
Т	NC	NC	V _{SS}	NC	NC	LBO	PE	NC	V _{SS}	NC	NC	т
U	NC	NC	NC	A12	NC	A11	A18	A10	NC	NC	NC	U
V	NC	NC	A9	A8	A7	A1	A6	A5	A4	NC	NC	V
W	NC	NC	TMS	TDI	A3	A0	A2	TDO	ТСК	NC	NC	W

11 x 19 Bump BGA—14 x 22 mm² Body—1 mm Bump Pitch



GS8322Z18/36/72 209-Bump BGA Pin Description

Pin Location	Symbol	Туре	Description
W6, V6	A0, A1	I	Address field LSBs and Address Counter Preset Inputs.
W7, W5, V9, V8, V7, V5, V4, V3, U8, U6, U4, A3, A5, A7, B7, A9, U7	An	I	Address Inputs
B5	A19	I	Address Inputs (x36/x18 Versions)
C7	A20	I	Address Inputs (x18 Version)
L11, M11, N11, P11, L10, M10, N10, P10, R10 A10, B10, C10, D10, A11, B11, C11, D11, E11 J1, H1, G1, F1, J2, H2, G2, F2, E2 W2, V2, U2, T2, W1, V1, U1, T1, R1 W10, V10, U10, T10, W11, V11, U11, T11, R11 J11, H11, G11, F11, J10, H10, G10, F10, E10 A2, B2, C2, D2, A1, B1, C1, D1, E1 L1, M1, N1, P1, L2, M2, N2, P2, R2	DQA1-DQA9 DQB1-DQB9 DQC1-DQC9 DQD1-DQD9 DQE1-DQE9 DQF1-DQF9 DQG1-DQG9 DQH1-DQH9	I/O	Data Input and Output pins (x72 Version)
L11, M11, N11, P11, L10, M10, N10, P10, R10 A10, B10, C10, D10, A11, B11, C11, D11, E11 J1, H1, G1, F1, J2, H2, G2, F2, E2 W2, V2, U2, T2, W1, V1, U1, T1, R1	DQA1—DQA9 DQB1—DQB9 DQC1—DQC9 DQD1—DQD9	I/O	Data Input and Output pins (x36 Version)
L11, M11, N11, P11, L10, M10, N10, P10, R10 J1, H1, G1, F1, J2, H2, G2, F2, E2	DQa1—DQa9 DQb1—DQb9	I/O	Data Input and Output pins (x18 Version)
C9, B8	Bа, Bв	I	Byte Write Enable for DQA, DQB I/Os; active low
B3, C4	Bc,BD	I	Byte Write Enable for DQc, DQ⊵ I/Os; active low (x72/x36 Versions)
C8, B9, B4, C3	Бе, Бг, Бд, Вн	I	Byte Write Enable for DQE, DQF, DQG, DQH I/Os; active low (x72 Version)
B5	NC	—	No Connect (x72 Version)
C7	NC	_	No Connect (x72/x36 Versions)
W10, V10, U10, T10, W11, V11, U11, T11, R11 J11, H11, G11, F11, J10, H10, G10, F10, E10 A2, B2, C2, D2, A1, B1, C1, D1, E1 L1, M1, N1, P1, L2, M2, N2, P2, R2, C8, B9, B4, C3	NC	_	No Connect (x36/x18 Versions)
B3, C4	NC	_	No Connect (x18 Version)
C5, D4, D5, D7, D8, K1, K2, K4, K8, K9, K10, K11, T4, T5, T7, T8, U3, U5, U9	NC	_	No Connect
К3	СК		Clock Input Signal; active high
C6	Chip Enable; active low		
A8	Ē3	I	Chip Enable; active low
A4	E2	I	Chip Enable; active high
D6	G	I	Output Enable; active low
A6	ADV		Burst address counter advance enable

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Specifications cited are subject to change without notice. For latest documentation see http://www.gsitechnology.com.



GS8322Z18/36/72 209-Bump BGA Pin Description

Pin Location	Symbol	Туре	Description
P6	ZZ	I	Sleep Mode control; active high
L6	FT	I	Flow Through or Pipeline mode; active low
T6	LBO	I	Linear Burst Order mode; active low
G6, J6	MCH	I	Must Connect High
N6	MCH	I	Must Connect High
H6, J6, K6, M6	MCL		Must Connect Low
A8, N6	MCL		Must Connect Low (x18 version)
B6	W	I	Write Enable; active low
Т7	PE	I	Parity Bit Enable; active low (High = x16/32 Mode, Low = x18/36 Mode)
F6	ZQ	I	FLXDrive Output Impedance Control (Low = Low Impedance [High Drive], High = High Impedance [Low Drive])
W3	TMS	I	Scan Test Mode Select
W4	TDI	I	Scan Test Data In
W8	TDO	0	Scan Test Data Out
W9	TCK	I	Scan Test Clock
E5, E6, E7, G5, G7, J5, J7, L5, L7, N5, N7, R5, R6, R7	V _{DD}	I	Core power supply
D3, D9, F3, F4, F5, F7, F8, F9, H3, H4, H5, H7, H8, H9, K5, K7, M3, M4, M5, M7, M8, M9, P3, P4, P5, P7, P8, P9, T3, T9	V _{SS}	I	I/O and Core Ground
E3, E4, E8, E9, G3, G4, G8, G9, J3, J4, J8, J9, L3, L4, L8, L9, N3, N4, N8, N9, R3, R4, R8, R9	V _{DDQ}	I	Output driver power supply

TECHNOLOGY

GS8322Z36B Pad Out 119-Bump BGA—Top View

	1	2	3	4	5	6	7	_
А	V _{DDQ}	A6	A7	A18	A8	A9	V _{DDQ}	А
В	NC	E2	A4	ADV	A15	E3	NC	В
С	NC	A5	A3	V _{DD}	A14	A16	NC	С
D	DQC	DQPC	V _{SS}	ZQ	V_{SS}	DQPB	DQB	D
Е	DQC	DQC	V _{SS}	E1	V_{SS}	DQB	DQB	E
F	V _{DDQ}	DQC	V _{SS}	G	V_{SS}	DQB	V _{DDQ}	F
G	DQC	DQC	BC	A17	BB	DQB	DQB	G
Н	DQC	DQC	V_{SS}	W	V_{SS}	DQB	DQB	Н
J	V _{DDQ}	V _{DD}	NC	V _{DD}	NC	V _{DD}	V _{DDQ}	J
К	DQD	DQD	V _{SS}	СК	V_{SS}	DQA	DQA	К
L	DQD	DQD	BD	NC	BA	DQA	DQA	L
М	V _{DDQ}	DQD	V _{SS}	CKE	V_{SS}	DQA	V _{DDQ}	М
Ν	DQD	DQD	V _{SS}	A1	V_{SS}	DQA	DQA	Ν
Ρ	DQD	DQPD	V _{SS}	A0	V_{SS}	DQPA	DQA	Ρ
R	NC	A2	LBO	V _{DD}	FT	A13	PE	R
Т	NC	NC	A10	A11	A12	A19	ZZ	Т
U	V _{DDQ}	TMS	TDI	ТСК	TDO	NC	V _{DDQ}	U

7 x 17 Bump BGA—14 x 22 mm² Body—1.27 mm Bump Pitch

TECHNOLOGY

GS8322Z18B Pad Out 119-Bump BGA—Top View

	1	2	3	4	5	6	7	_
А	V _{DDQ}	A6	A7	A18	A8	A9	V _{DDQ}	А
В	NC	E2	A4	ADV	A15	E3	NC	В
С	NC	A5	A3	V_{DD}	A14	A16	NC	С
D	DQB	NC	V _{SS}	ZQ	V_{SS}	DQPA	NC	D
E	NC	DQB	V _{SS}	E1	V _{SS}	NC	DQA	E
F	V _{DDQ}	NC	V _{SS}	G	V _{SS}	DQA	V _{DDQ}	F
G	NC	DQB	BB	A17	NC	NC	DQA	G
Н	DQB	NC	V _{SS}	\overline{W}	V_{SS}	DQA	NC	Н
J	V _{DDQ}	V _{DD}	NC	V _{DD}	NC	V _{DD}	V _{DDQ}	J
К	NC	DQB	V _{SS}	СК	V _{SS}	NC	DQA	К
L	DQB	NC	NC	NC	BA	DQA	NC	L
М	V _{DDQ}	DQB	V_{SS}	CKE	V_{SS}	NC	V _{DDQ}	М
Ν	DQB	NC	V _{SS}	A1	V_{SS}	DQA	NC	Ν
Ρ	NC	DQPB	V _{SS}	A0	V_{SS}	NC	DQA	Р
R	NC	A2	LBO	V_{DD}	FT	A13	PE	R
Т	NC	A10	A11	A20	A12	A19	ZZ	Т
U	V _{DDQ}	TMS	TDI	ТСК	TDO	NC	V _{DDQ}	U

7 x 17 Bump BGA—14 x 22 mm² Body—1.27 mm Bump Pitch



GS8322Z18/36 119-Bump BGA Pin Description

Pin Location	Symbol	Туре	Description
P4, N4	A0, A1	Ι	Address field LSBs and Address Counter Preset Inputs
R2, C3, B3, C2, A2, A3, A5, A6, T3, T5, R6, C5, B5, C6, G4, A4	An	l	Address Inputs
T4, T6	An		Address Input (x36 Version)
T2	NC		No Connect (x36 Version)
T2, T6, T4	An	Ι	Address Input (x18 Version)
K7, L7, N7, P7, K6, L6, M6, N6 H7, G7, E7, D7, H6, G6, F6, E6 H1, G1, E1, D1, H2, G2, F2, E2 K1, L1, N1, P1, K2, L2, M2, N2	DQA1–DQA8 DQB1–DQB8 DQc1–DQc8 DQD1–DQD8	I/O	Data Input and Output pins. (x36 Version)
P6, D6, D2, P2	DQA9, DQB9, DQc9, DQD9	I/O	Data Input and Output pins. (x36 Version)
L5, G5, G3, L3	Ba, Bb, Bc, Bd	I	Byte Write Enable for DQA, DQB, DQc, DQD I/Os; active low (x36 Version)
P7, N6, L6, K7, H6, G7, F6, E7, D6 D1, E2, G2, H1, K2, L1, M2, N1, P2	DQA1–DQA9 DQB1–DQB9	I/O	Data Input and Output pins (x18 Version)
L5, G3	Bа, Bв	-	Byte Write Enable for DQA, DQB I/Os; active low (x18 Version)
B1, C1, R1, T1, U6, B7, C7, J3, J5	NC		No Connect
P6, N7, M6, L7, K6, H7, G6, E6, D7, D2, E1, F2, G1, H2, K1, L2, N2, P1, G5, L3	NC	_	No Connect (x18 Version)
L4	NC	_	No Connect
К4	СК	I	Clock Input Signal; active high
M4	CKE	I	Clock Enable; active low
H4	W	Ι	Write Enable; active low
E4	Ē1	Ι	Chip Enable; active low
B6	E3	Ι	Chip Enable; active low
B2	E2	-	Chip Enable; active high
F4	G	I	Output Enable; active low
B4	ADV		Burst address counter advance enable
Τ7	ZZ		Sleep mode control; active high
R5	FT	I	Flow Through or Pipeline mode; active low
R3	LBO	I	Linear Burst Order mode; active low
D4	ZQ	I	FLXDrive Output Impedance Control (Low = Low Impedance [High Drive], High = High Impedance [Low Drive])
R7	PE	Ι	Parity Bit Enable; active low



GS8322Z18/36 119-Bump BGA Pin Description

Pin Location	Symbol	Туре	Description
U2	TMS	I	Scan Test Mode Select
U3	TDI	I	Scan Test Data In
U5	TDO	0	Scan Test Data Out
U4	TCK	I	Scan Test Clock
J2, C4, J4, R4, J6	V _{DD}	I	Core power supply
D3, E3, F3, H3, K3, M3, N3, P3, D5, E5, F5, H5, K5, M5, N5, P5	V _{SS}	I	I/O and Core Ground
A1, F1, J1, M1, U1, A7, F7, J7, M7, U7	V _{DDQ}	I	Output driver power supply

BPR1999.05.18

Functional Details

Clocking

Deassertion of the Clock Enable ($\overline{\text{CKE}}$) input blocks the Clock input from reaching the RAM's internal circuits. It may be used to suspend RAM operations. Failure to observe Clock Enable set-up or hold requirements will result in erratic operation.

Pipeline Mode Read and Write Operations

All inputs (with the exception of Output Enable, Linear Burst Order and Sleep) are synchronized to rising clock edges. Single cycle read and write operations must be initiated with the Advance/Load pin (ADV) held low, in order to load the new address. Device activation is accomplished by asserting all three of the Chip Enable inputs (\overline{E}_1 , \overline{E}_2 , and \overline{E}_3). Deassertion of any one of the Enable inputs will deactivate the device.

Function	W	BA	Вв	Bc	BD
Read	Н	Х	Х	Х	Х
Write Byte "a"	L	L	Н	Н	Н
Write Byte "b"	L	Н	L	Н	Н
Write Byte "c"	L	Н	Н	L	Н
Write Byte "d"	L	Н	Н	Н	L
Write all Bytes	L	L	L	L	L
Write Abort/NOP	L	Н	Н	Н	Н

Read operation is initiated when the following conditions are satisfied at the rising edge of clock: $\overline{\text{CKE}}$ is asserted low, all three chip enables ($\overline{\text{E1}}$, $\overline{\text{E2}}$, and $\overline{\text{E3}}$) are active, the write enable input signals $\overline{\text{W}}$ is deasserted high, and ADV is asserted low. The address presented to the address inputs is latched into the address register and presented to the memory core and control logic. The control logic determines that a read access is in progress and allows the requested data to propagate to the input of the output register. At the next rising edge of clock the read data is allowed to propagate through the output register and onto the output pins.

Write operation occurs when the RAM is selected, CKE is active, and the Write input is sampled low at the rising edge of clock.



The Byte Write Enable inputs ($\overline{B}A$, $\overline{B}B$, $\overline{B}C$, and $\overline{B}D$) determine which bytes will be written. All or none may be activated. A write cycle with no Byte Write inputs active is a no-op cycle. The pipelined NBT SRAM provides double late write functionality, matching the write command versus data pipeline length (2 cycles) to the read command versus data pipeline length (2 cycles). At the first rising edge of clock, Enable, Write, Byte Write(s), and Address are registered. The Data In associated with that address is required at the third rising edge of clock.

Flow Through Mode Read and Write Operations

Operation of the RAM in Flow Through mode is very similar to operations in Pipeline mode. Activation of a Read Cycle and the use of the Burst Address Counter is identical. In Flow Through mode the device may begin driving out new data immediately after new address are clocked into the RAM, rather than holding new data until the following (second) clock edge. Therefore, in Flow Through mode the read pipeline is one cycle shorter than in Pipeline mode.

Write operations are initiated in the same way, but differ in that the write pipeline is one cycle shorter as well, preserving the ability to turn the bus from reads to writes without inserting any dead cycles. While the pipelined NBT RAMs implement a double late write protocol in Flow Through mode a single late write protocol mode is observed. Therefore, in Flow Through mode, address and control are registered on the first rising edge of clock and data in is required at the data input pins at the second rising edge of clock.



Synchronous Truth Table

Operation	Туре	Address	Ē1	E2	Ē3	ZZ	ADV	W	Bx	G	CKE	СК	DQ	Notes
Deselect Cycle, Power Down	D	None	Н	Х	Х	L	L	Х	Х	Х	L	L-H	High-Z	
Deselect Cycle, Power Down	D	None	Х	Х	Н	L	L	Х	Х	Х	L	L-H	High-Z	
Deselect Cycle, Power Down	D	None	Х	L	Х	L	L	Х	Х	Х	L	L-H	High-Z	
Deselect Cycle, Continue	D	None	Х	Х	Х	L	Н	Х	Х	Х	L	L-H	High-Z	1
Read Cycle, Begin Burst	R	External	L	Н	L	L	L	Н	Х	L	L	L-H	Q	
Read Cycle, Continue Burst	В	Next	Х	Х	Х	L	Н	Х	Х	L	L	L-H	Q	1,10
NOP/Read, Begin Burst	R	External	L	Н	L	L	L	Н	Х	Н	L	L-H	High-Z	2
Dummy Read, Continue Burst	В	Next	Х	Х	Х	L	Н	Х	Х	Н	L	L-H	High-Z	1,2,10
Write Cycle, Begin Burst	W	External	L	Н	L	L	L	L	L	Х	L	L-H	D	3
Write Cycle, Continue Burst	В	Next	Х	Х	Х	L	Н	Х	L	Х	L	L-H	D	1,3,10
NOP/Write Abort, Begin Burst	W	None	L	Н	L	L	L	L	Н	Х	L	L-H	High-Z	2,3
Write Abort, Continue Burst	В	Next	Х	Х	Х	L	Н	Х	Н	Х	L	L-H	High-Z	1,2,3,10
Clock Edge Ignore, Stall		Current	Х	Х	Х	L	Х	Х	Х	Х	Н	L-H	-	4
Sleep Mode		None	Х	Х	Х	Н	Х	Х	Х	Х	Х	Х	High-Z	

Notes:

1. Continue Burst cycles, whether Read or Write, use the same control inputs. A Deselect continue cycle can only be entered into if a Deselect cycle is executed first.

2. Dummy Read and Write abort can be considered NOPs because the SRAM performs no operation. A Write abort occurs when the W pin is sampled low but no Byte Write pins are active, so no write operation is performed.

3. G can be wired low to minimize the number of control signals provided to the SRAM. Output drivers will automatically turn off during write cycles.

4. If CKE High occurs during a pipelined read cycle, the DQ bus will remain active (Low Z). If CKE High occurs during a write cycle, the bus will remain in High Z.

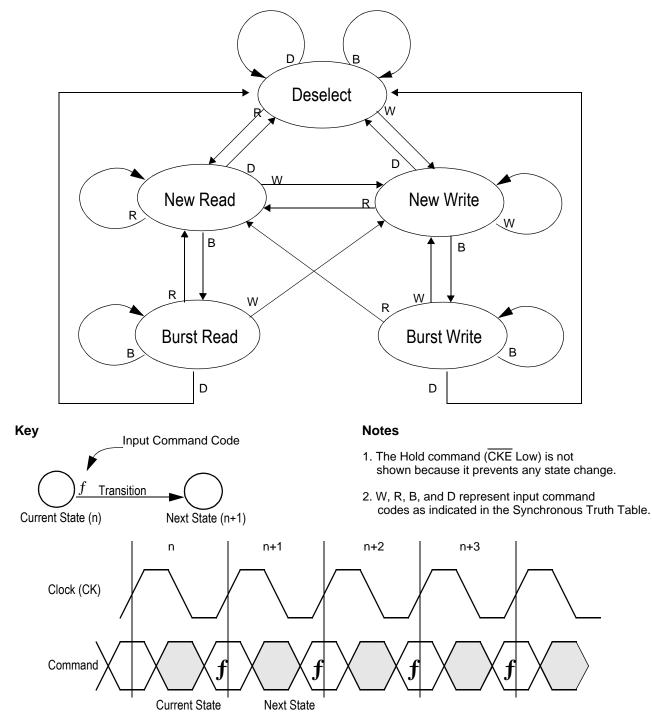
5. X = Don't Care; H = Logic High; L = Logic Low; Bx = High = All Byte Write signals are high; Bx = Low = One or more Byte/Write signals are Low

6. All inputs, except G and ZZ must meet setup and hold times of rising clock edge.

- 7. Wait states can be inserted by setting CKE high.
- 8. This device contains circuitry that ensures all outputs are in High Z during power-up.
- 9. A 2-bit burst counter is incorporated.
- 10. The address counter is incriminated for all Burst continue cycles.



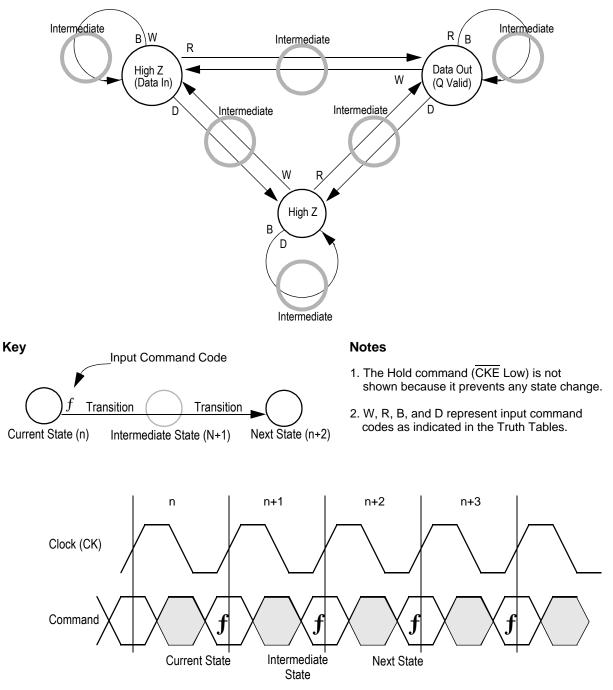
Pipelined and Flow Through Read Write Control State Diagram



Current State and Next State Definition for Pipelined and Flow through Read/Write Control State Diagram



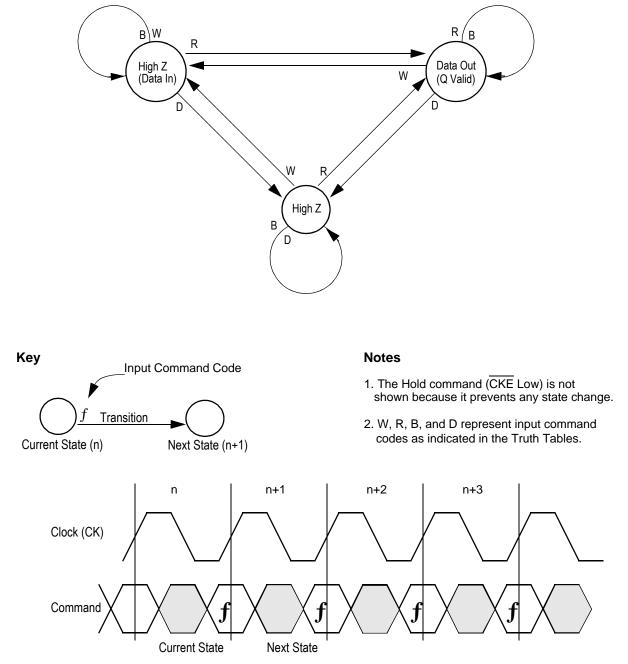
Pipeline Mode Data I/O State Diagram



Current State and Next State Definition for Pipeline Mode Data I/O State Diagram



Flow Through Mode Data I/O State Diagram



Current State and Next State Definition for: Pipeline and Flow Through Read Write Control State Diagram



Burst Cycles

Although NBT RAMs are designed to sustain 100% bus bandwidth by eliminating turnaround cycle when there is transition from read to write, multiple back-to-back reads or writes may also be performed. NBT SRAMs provide an on-chip burst address generator that can be utilized, if desired, to further simplify burst read or write implementations. The ADV control pin, when driven high, commands the SRAM to advance the internal address counter and use the counter generated address to read or write the SRAM. The starting address for the first cycle in a burst cycle series is loaded into the SRAM by driving the ADV pin low, into Load mode.

Burst Order

The burst address counter wraps around to its initial state after four addresses (the loaded address and three more) have been accessed. The burst sequence is determined by the state of the Linear Burst Order pin (LBO). When this pin is Low, a linear burst sequence is selected. When the RAM is installed with the LBO pin tied high, Interleaved burst sequence is selected. See the tables below for details.

FLXDrive™

The ZQ pin allows selection between NBT RAM nominal drive strength (ZQ low) for multi-drop bus applications and low drive strength (ZQ floating or high) point-to-point applications. See the Output Driver Characteristics chart for details.

Mode	Pin	Functions
mode		

Mode Name	Pin Name	State	Function
Burst Order Control	LBO	L	Linear Burst
Buist Order Control	LDO	Н	Interleaved Burst
Output Register Control	FT	L	Flow Through
Culput Register Control	ГІ	H or NC	Pipeline
Device Device Control	77	L or NC	Active
Power Down Control	ZZ	Н	Standby, I _{DD} = I _{SB}
Dority Epoble	PE	L or NC	Activate 9th I/O's (x18/36 Mode)
Parity Enable	FE	Н	Deactivate 9th I/O's (x16/32 Mode)
FLXDrive Output Impedance Control	ZQ	L	High Drive (Low Impedance)
	20	H or NC	Low Drive (High Impedance)

Note:

There are pull-up devices on the ZQ and \overline{FT} pins and a pull-down devices on the \overline{PE} and ZZ pins, so those input pins can be unconnected and the chip will operate in the default states as specified in the above tables.

Enable / Disable Parity I/O Pins

This SRAM allows the user to configure the device to operate in Parity I/O active (x18, x36, or x72) or in Parity I/O inactive (x16, x32, or x64) mode. Holding the \overline{PE} bump low or letting it float will activate the 9th I/O on each byte of the RAM. Grounding \overline{PE} deactivates the 9th I/O of each byte, although the bit in each byte of the memory array remains active to store and recall parity bits generated and read into the ByteSafe parity circuits.



Burst Counter Sequences

Linear Burst Sequence

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	10	11	00
3rd address	10	11	00	01
4th address	11	00	01	10

Note: The burst counter wraps to initial state on the 5th clock.

Interleaved Burst Sequence

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	00	11	10
3rd address	10	11	00	01
4th address	11	10	01	00

Note: The burst counter wraps to initial state on the 5th clock.

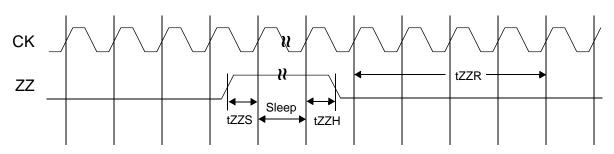
BPR 1999.05.18

Sleep Mode

During normal operation, ZZ must be pulled low, either by the user or by its internal pull down resistor. When ZZ is pulled high, the SRAM will enter a Power Sleep mode after 2 cycles. At this time, internal state of the SRAM is preserved. When ZZ returns to low, the SRAM operates normally after 2 cycles of wake up time.

Sleep mode is a low current, power-down mode in which the device is deselected and current is reduced to $I_{SB}2$. The duration of Sleep mode is dictated by the length of time the ZZ is in a High state. After entering Sleep mode, all inputs except ZZ become disabled and all outputs go to High-Z The ZZ pin is an asynchronous, active high input that causes the device to enter Sleep mode. When the ZZ pin is driven high, $I_{SB}2$ is guaranteed after the time tZZI is met. Because ZZ is an asynchronous input, pending operations or operations in progress may not be properly completed if ZZ is asserted. Therefore, Sleep mode must not be initiated until valid pending operations are completed. Similarly, when exiting Sleep mode during tZZR, only a Deselect or Read commands may be applied while the SRAM is recovering from Sleep mode.

Sleep Mode Timing Diagram



Designing for Compatibility

The GSI NBT SRAMs offer users a configurable selection between Flow Through mode and Pipeline mode via the $\overline{\text{FT}}$ signal found on Bump 5R. Not all vendors offer this option, however most mark Bump 5R as V_{DD} or V_{DDQ} on pipelined parts and V_{SS} on flow through parts. GSI NBT SRAMs are fully compatible with these sockets.



Absolute Maximum Ratings

(All voltages reference to V_{SS})

Symbol	Description	Value	Unit
V _{DD}	Voltage on V _{DD} Pins	0.5 to 4.6	V
V _{DDQ}	Voltage in V _{DDQ} Pins	0.5 to 4.6	V
V _{CK}	Voltage on Clock Input Pin	-0.5 to 6	V
V _{I/O}	Voltage on I/O Pins	-0.5 to V _{DDQ} +0.5 (\leq 4.6 V max.)	V
V _{IN}	Voltage on Other Input Pins	-0.5 to V _{DD} +0.5 (\leq 4.6 V max.)	V
I _{IN}	Input Current on Any Pin	+/20	mA
I _{OUT}	Output Current on Any I/O Pin	+/20	mA
P _D	Package Power Dissipation	1.5	W
T _{STG}	Storage Temperature	-55 to 125	٥C
T _{BIAS}	Temperature Under Bias	-55 to 125	٥C

Note:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Absolute Maximum Ratings, for an extended period of time, may affect reliability of this component.



Power Supply Voltage Ranges

Parameter	Symbol	Min.	Тур.	Max.	Unit	Notes
3.3 V Supply Voltage	V _{DD3}	3.0	3.3	3.6	V	
2.5 V Supply Voltage	V _{DD2}	2.3	2.5	2.7	V	
3.3 V V _{DDQ} I/O Supply Voltage	V _{DDQ3}	3.0	3.3	3.6	V	
2.5 V V _{DDQ} I/O Supply Voltage	V _{DDQ2}	2.4	2.5	2.7	V	

Notes:

1. The part numbers of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

2. Input Under/overshoot voltage must be -2 V > Vi < V_{DDn}+2 V not to exceed 4.6 V maximum, with a pulse width not to exceed 20% tKC.

V_{DDQ3} Range Logic Levels

Parameter	Symbol	Min.	Тур.	Max.	Unit	Notes
V _{DD} Input High Voltage	V _{IH}	1.7		V _{DD} + 0.3	V	1
V _{DD} Input Low Voltage	V _{IL}	-0.3	_	0.8	V	1
V _{DDQ} I/O Input High Voltage	V _{IHQ}	1.7	_	V _{DDQ} + 0.3	V	1,3
V _{DDQ} I/O Input Low Voltage	V _{ILQ}	-0.3		0.8	V	1,3

Notes:

1. The part numbers of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

2. Input Under/overshoot voltage must be -2 V > Vi < V_{DDn}+2 V not to exceed 4.6 V maximum, with a pulse width not to exceed 20% tKC.

3. V_{IHQ} (max) is voltage on V_{DDQ} pins plus 0.3 V.

V_{DDQ2} Range Logic Levels

Parameter	Symbol	Min.	Тур.	Max.	Unit	Notes
V _{DD} Input High Voltage	V _{IH}	0.6*V _{DD}		V _{DD} + 0.3	V	1
V _{DD} Input Low Voltage	V _{IL}	-0.3		0.3*V _{DD}	V	1
V _{DDQ} I/O Input High Voltage	V _{IHQ}	0.6*V _{DD}		V _{DDQ} + 0.3	V	1,3
V _{DDQ} I/O Input Low Voltage	V _{ILQ}	-0.3	_	0.3*V _{DD}	V	1,3

Notes:

1. The part numbers of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

2. Input Under/overshoot voltage must be -2 V > Vi < V_{DDn}+2 V not to exceed 4.6 V maximum, with a pulse width not to exceed 20% tKC.

3. V_{IHQ} (max) is voltage on V_{DDQ} pins plus 0.3 V.



Recommended Operating Temperatures

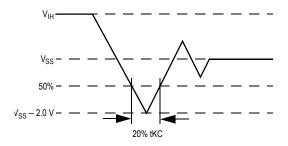
Parameter	Symbol	Min.	Тур.	Max.	Unit	Notes
Ambient Temperature (Commercial Range Versions)	Τ _Α	0	25	70	°C	2
Ambient Temperature (Industrial Range Versions)	Τ _Α	-40	25	85	°C	2

Note:

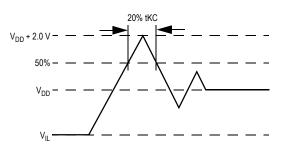
1. The part numbers of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

2. Input Under/overshoot voltage must be -2 V > Vi < V_{DDn}+2 V not to exceed 4.6 V maximum, with a pulse width not to exceed 20% tKC.

Undershoot Measurement and Timing



Overshoot Measurement and Timing



Capacitance

(T_A = 25°C, f = 1 MHz, V_{DD} = 2.5 V)

Parameter	Symbol	Test conditions	Тур.	Max.	Unit
Input Capacitance	C _{IN}	V _{IN} = 0 V	4	5	pF
Input/Output Capacitance	C _{I/O}	V _{OUT} = 0 V	6	7	pF

Note: These parameters are sample tested.

Package Thermal Characteristics

Rating	Layer Board	Symbol	Max	Unit	Notes
Junction to Ambient (at 200 lfm)	single	R_{\ThetaJA}	40	°C/W	1,2
Junction to Ambient (at 200 lfm)	four	R_{\ThetaJA}	24	°C/W	1,2
Junction to Case (TOP)		R_{\ThetaJC}	9	°C/W	3

Notes:

1. Junction temperature is a function of SRAM power dissipation, package thermal resistance, mounting board temperature, ambient. Temperature air flow, board density, and PCB thermal resistance.

2. SCMI G-38-87

3. Average thermal resistance between die and top surface, MIL SPEC-883, Method 1012.1

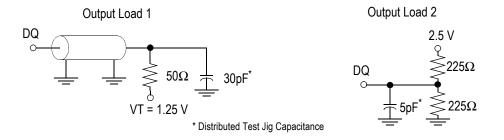


AC Test Conditions

Parameter	Conditions
Input high level	2.3 V
Input low level	0.2 V
Input slew rate	1 V/ns
Input reference level	1.25 V
Output reference level	1.25 V
Output load	Fig. 1& 2

Notes:

- 1. Include scope and jig capacitance.
- Test conditions as specified with output loading as shown in Fig. 1 unless otherwise noted.
- 3. Output Load 2 for t_{LZ} , t_{HZ} , t_{OLZ} and t_{OHZ}
- 4. Device is deselected as defined by the Truth Table.



DC Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Max
Input Leakage Current (except mode pins)	Ι _L	$V_{IN} = 0$ to V_{DD}	—1 uA	1 uA
ZZ and PE Input Current	I _{IN1}	$\begin{array}{l} V_{DD} \geq V_{IN} \geq V_{IH} \\ 0 \ V \leq V_{IN} \leq V_{IH} \end{array}$	—1 uA —1 uA	1 uA 100 uA
FT, SCD, ZQ Input Current	I _{IN2}	$\begin{array}{l} V_{DD} \geq V_{IN} \geq V_{IL} \\ 0 \ V \leq V_{IN} \leq V_{IL} \end{array}$	−100 uA −1 uA	1 uA 1 uA
Output Leakage Current	I _{OL}	Output Disable, $V_{OUT} = 0$ to V_{DD}	—1 uA	1 uA
Output High Voltage	V _{OH2}	I _{OH} = —8 mA, V _{DDQ} = 2.375 V	1.7 V	—
Output High Voltage	V _{OH3}	I _{OH} = –8 mA, V _{DDQ} = 3.135 V	2.4 V	
Output Low Voltage	V _{OL}	I _{OL} = 8 mA	_	0.4 V



Operating Currents

Product Preview GS8322Z18(B/C)/GS8322Z36(B/C)/GS8322Z72(C)

						-2	-250	-225	25	-200	00	-1(-166	-150	0	-133		
							3		2		2		2		2			
	Parameter	Test Conditions		Mode	Symbol	о ф	4 4 5	- 5	64 t	o 9	64 64 0	о 9	-40 t	- 9	₽ ₽	о 9	64 t	Unit
						70°C	85°C	70°C	85°C	70°C	85°C	70°C	85°C	70°C	85°C	70°C	85°C	
00 10/20			\627)	Pipeline	loo Iooa	580 80	560 80	530 70	550 70	480 60	500 60	410 50	430 50	380 50	400 50	340 40	360 40	MM
01			(212)	Flow Through	aa ^l Doa	310 40	330 40	340 40	330 40	270 30	290 30	270 30	290 30	270 30	290 30	200 20	220 20	MM
	Operating Current	Device Selected; All other inputs	(26)	Pipeline	aal Doa	520 40	540 40	470 40	490 40	430 30	450 30	370 30	390 30	340 30	360 30	310 20	330 20	MM
	3.3 V	≥V _{IH} or ≤ V _{IL} Output open	(nex)	Flow Through	loo Iooa	280 20	300 20	280 20	300 20	250 20	270 20	350 20	270 20	250 20	270 20	180 20	200 20	MM
			(18)	Pipeline	loo Iooa	345 20	360 20	315 20	330 20	290 15	305 15	250 15	265 15	230 15	245 15	205 10	220 10	ША
			(01.4)	Flow Through	loo Iooa	200 10	215 10	200 10	215 10	175 10	190 10	175 10	190 10	175 10	190 10	135 10	150 10	MM
22/42			(77)	Pipeline	loo Iooa	580 60	600 60	530 60	550 60	480 50	500 50	410 40	430 40	380 40	400 40	340 30	360 30	MM
			12121	Flow Through	loo Doa	310 30	330 30	310 30	330 30	270 30	290 30	270 30	290 30	270 30	290 30	200 20	220 20	ША
	Operating Current	Device Selected; All other inputs	(927)	Pipeline	loo Iooq	520 30	540 30	470 30	490 30	430 30	450 30	370 20	390 20	340 20	360 20	310 20	330 20	mA
	2.5 V	≥V _{IH} or ≤ V _{IL} Output open		Flow Through	loo Iooa	280 20	300 20	280 20	300 20	250 20	270 20	250 20	270 20	250 20	270 20	180 10	200 10	MM
			(~18)	Pipeline	loo Iooa	345 15	360 15	315 15	330 15	290 15	305 15	250 10	265 10	230 10	245 10	205 10	220 10	MM
			(01.4)	Flow Through	loo Iooa	200 10	215 10	200 10	215 10	175 10	190 10	175 10	190 10	175 10	190 10	135 5	150 5	MM
2001	Standby			Pipeline	I _{SB}	40	60	40	60	40	60	40	60	40	60	40	60	ШA
Cigo	Current	<i>∠</i> ∠ ≥ V _{DD} – 0.2 V		Flow Through	ISB	40	09	40	60	40	60	40	60	40	60	40	60	ШA
`omio	Deselect	Device Deselected;		Pipeline	مما	170	180	160	170	150	160	130	140	120	130	100	110	ШA
a malu atu	Current	All other inputs ≥ V _{IH} or ≤ V _{IL}		Flow Through	مما	120	130	120	130	100	110	100	110	100	110	06	100	mA
or, Inc.	Notes: 1. I _{DD} and I 2. All param	s: I _{DD} and I _{DDQ} apply to any combination of V _{DD3} , V _{DD2} , V _{DDQ3} , and V _{DDQ2} operation. All parameters listed are worst case scenario.	bination case so	of V _{DD3} , V _{DC} enario.	12, Voda3, é	and V _{DD}	Q2 opers	ation.										

Rev: 1.00 10/2001 22/42 Specifications cited are subject to change without notice. For latest documentation see http://www.gsitechnology.com. © 2001, Giga Semiconductor, Inc.

TECHNOLOGY

AC Electrical Characteristics

	Parameter	Symbol	-2	50	-22	25	-20	00	-16	6	-1	50	-1	33	Unit
	Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
	Clock Cycle Time	tKC	4.0	—	4.4	—	5.0	—	6.0	—	6.7	—	7.5	—	ns
Distaliant	Clock to Output Valid	tKQ	_	2.3		2.5		3.0	_	3.4		3.8		4.0	ns
Pipeline	Clock to Output Invalid	tKQX	1.5	—	1.5	_	1.5	—	1.5	—	1.5		1.5	—	ns
	Clock to Output in Low-Z	tLZ ¹	1.5	_	1.5	_	1.5	—	1.5	_	1.5		1.5	—	ns
	Clock Cycle Time	tKC	7.0	—	7.5	—	8.5	—	10.0	—	10.0		15.0	—	ns
Flow	Clock to Output Valid	tKQ	—	6.0		6.0		7.5	_	8.5		10.0		10.0	ns
Through	Clock to Output Invalid	tKQX	3.0	—	3.0	_	3.0	—	3.0	—	3.0		3.0	—	ns
	Clock to Output in Low-Z	tLZ ¹	3.0	_	3.0	_	3.0	—	3.0	_	3.0		3.0	—	ns
	Clock HIGH Time	tKH	1.3	—	1.3	—	1.3	—	1.3	_	1.5	_	1.7	—	ns
	Clock LOW Time	tKL	1.5		1.5	—	1.5	—	1.5		1.7		2		ns
	Clock to Output in High-Z	tHZ ¹	1.5	2.3	1.5	2.5	1.5	3.0	1.5	3.5	1.5	3.8	1.5	4.0	ns
	G to Output Valid	tOE	—	2.3		2.5		3.2		3.5		3.8		4.0	ns
	G to output in Low-Z	tOLZ ¹	0	—	0		0	—	0		0	_	0	_	ns
	G to output in High-Z	tOHZ ¹		2.3		2.5		3.0		3.5		3.8		4.0	ns
	Setup time	tS	1.5	—	1.5	—	1.5	—	1.5	_	1.5	_	1.5	—	ns
	Hold time	tH	0.5		0.5	—	0.5	—	0.5		0.5		0.5		ns
	ZZ setup time	tZZS ²	5		5		5	—	5		5		5		ns
	ZZ hold time	tZZH ²	1	—	1	—	1	—	1	—	1	_	1	—	ns
	ZZ recovery	tZZR	100	—	100	—	100	—	100		100	—	100		ns

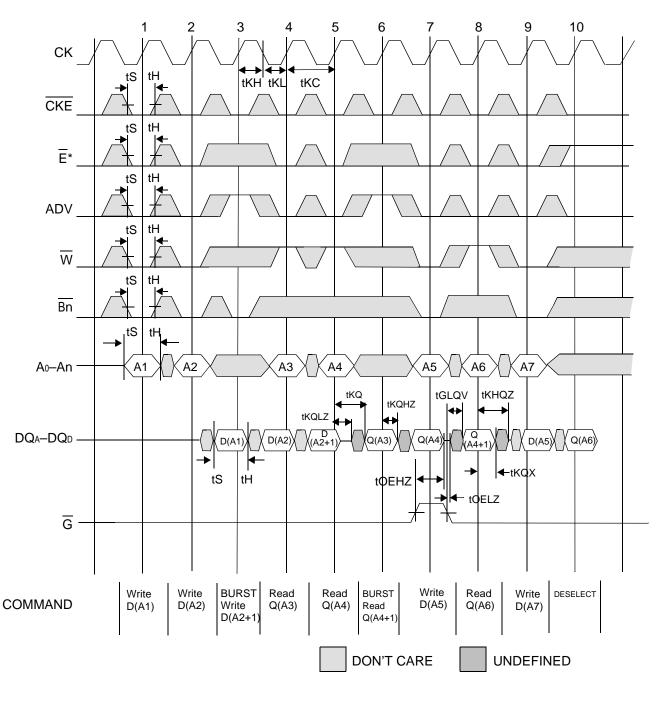
Notes:

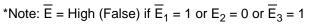
1. These parameters are sampled and are not 100% tested.

2. ZZ is an asynchronous signal. However, in order to be recognized on any given clock cycle, ZZ must meet the specified setup and hold times as specified above.



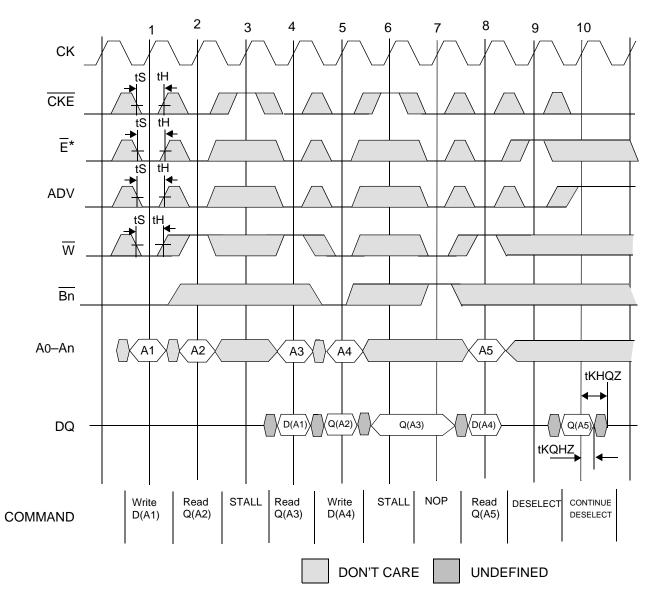
Pipeline Mode Read/Write Cycle Timing







Pipeline Mode No-Op, Stall and Deselect Timing

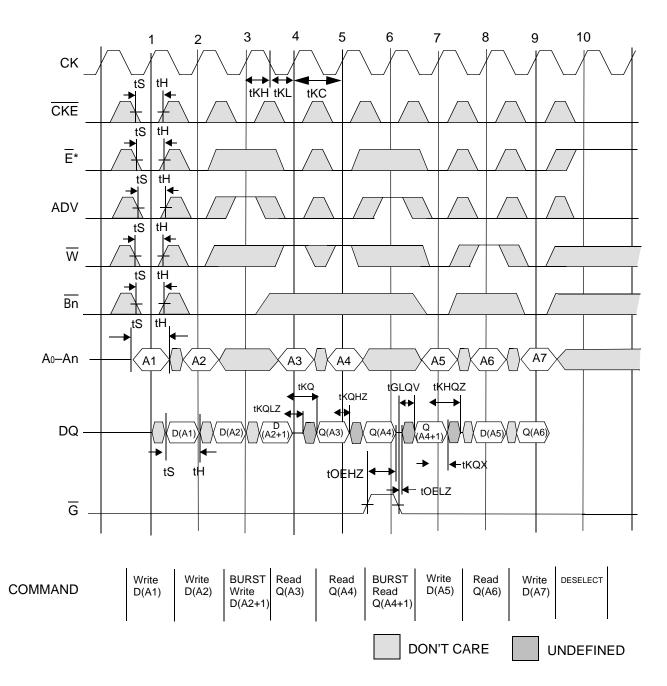


*Note: \overline{E} = High (False) if \overline{E}_1 = 1 or E_2 = 0 or \overline{E}_3 = 1

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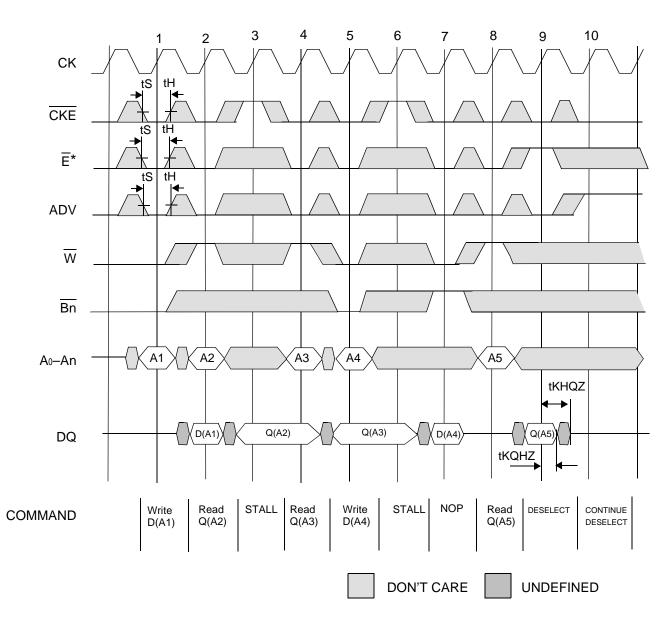
Flow Through Mode Read/Write Cycle Timing



*Note: \overline{E} = High (False) if \overline{E}_1 = 1 or E_2 = 0 or \overline{E}_3 = 1



Flow Through Mode No-Op, Stall and Deselect Timing



*Note: \overline{E} = High (False) if \overline{E}_1 = 1 or E_2 = 0 or \overline{E}_3 = 1



JTAG Port Operation

Overview

The JTAG Port on this RAM operates in a manner that is compliant with IEEE Standard 1149.1-1990, a serial boundary scan interface standard (commonly referred to as JTAG). The JTAG Port input interface levels scale with V_{DD} . The JTAG output drivers are powered by V_{DDO} .

Disabling the JTAG Port

It is possible to use this device without utilizing the JTAG port. The port is reset at power-up and will remain inactive unless clocked. TCK, TDI, and TMS are designed with internal pull-up circuits. To assure normal operation of the RAM with the JTAG Port unused, TCK, TDI, and TMS may be left floating or tied to either V_{DD} or V_{SS} . TDO should be left unconnected.

JTAG Pin Descriptions

Pin	Pin Name	I/O	Description
ТСК	Test Clock	In	Clocks all TAP events. All inputs are captured on the rising edge of TCK and all outputs propagate from the falling edge of TCK.
TMS	Test Mode Select	In	The TMS input is sampled on the rising edge of TCK. This is the command input for the TAP controller state machine. An undriven TMS input will produce the same result as a logic one input level.
TDI	Test Data In	In	The TDI input is sampled on the rising edge of TCK. This is the input side of the serial registers placed between TDI and TDO. The register placed between TDI and TDO is determined by the state of the TAP Controller state machine and the instruction that is currently loaded in the TAP Instruction Register (refer to the TAP Controller State Diagram). An undriven TDI pin will produce the same result as a logic one input level.
TDO	Test Data Out	Out	Output that is active depending on the state of the TAP state machine. Output changes in response to the falling edge of TCK. This is the output side of the serial registers placed between TDI and TDO.

Note:

This device does not have a TRST (TAP Reset) pin. TRST is optional in IEEE 1149.1. The Test-Logic-Reset state is entered while TMS is held high for five rising edges of TCK. The TAP Controller is also reset automaticly at power-up.

JTAG Port Registers

Overview

The various JTAG registers, refered to as Test Access Port or TAP Registers, are selected (one at a time) via the sequences of 1s and 0s applied to TMS as TCK is strobed. Each of the TAP Registers is a serial shift register that captures serial input data on the rising edge of TCK and pushes serial data out on the next falling edge of TCK. When a register is selected, it is placed between the TDI and TDO pins.

Instruction Register

The Instruction Register holds the instructions that are executed by the TAP controller when it is moved into the Run, Test/Idle, or the various data register states. Instructions are 3 bits long. The Instruction Register can be loaded when it is placed between the TDI and TDO pins. The Instruction Register is automatically preloaded with the IDCODE instruction at power-up or whenever the controller is placed in Test-Logic-Reset state.

Bypass Register

The Bypass Register is a single bit register that can be placed between TDI and TDO. It allows serial test data to be passed through the RAM's JTAG Port to another device in the scan chain with as little delay as possible.

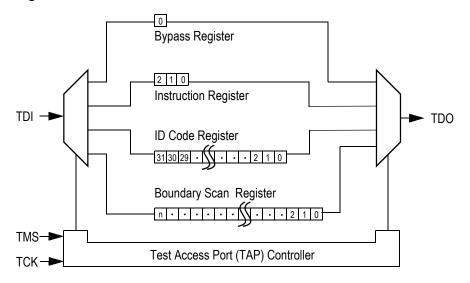
Rev: 1.00 10/2001	28/42	© 2001, Giga Semiconductor, Inc.
Specifications cited are subject to change without	but notice. For latest documentation see http://www.gsitechnology.com.	



Boundary Scan Register

The Boundary Scan Register is a collection of flip flops that can be preset by the logic level found on the RAM's input or I/O pins. The flip flops are then daisy chained together so the levels found can be shifted serially out of the JTAG Port's TDO pin. The Boundary Scan Register also includes a number of place holder flip flops (always set to a logic 1). The relationship between the device pins and the bits in the Boundary Scan Register is described in the Scan Order Table following. The Boundary Scan Register, under the control of the TAP Controller, is loaded with the contents of the RAMs I/O ring when the controller is in Capture-DR state and then is placed between the TDI and TDO pins when the controller is moved to Shift-DR state. SAMPLE-Z, SAMPLE/PRELOAD and EXTEST instructions can be used to activate the Boundary Scan Register.

JTAG TAP Block Diagram



Identification (ID) Register

The ID Register is a 32-bit register that is loaded with a device and vendor specific 32-bit code when the controller is put in Capture-DR state with the IDCODE command loaded in the Instruction Register. The code is loaded from a 32-bit on-chip ROM. It describes various attributes of the RAM as indicated below. The register is then placed between the TDI and TDO pins when the controller is moved into Shift-DR state. Bit 0 in the register is the LSB and the first to reach TDO when shifting begins.

ID Register Contents

		Revi	ie sion de	I						Not	Usec	1					Co		O urati	on				SI 1 ED I	EC		nd					Presence Register
Bit #	31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
x72	Х	Х	Х	Х	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	1	0	0	0	1	1	0	1	1	0	0	1	1
x36	Х	Х	Х	Х	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	1	1	0	1	1	0	0	1	1
x32	Х	Х	Х	Х	0	0	0	0	0	0	0	0	0	0	0	0	1	1	0	0	0	0	0	1	1	0	1	1	0	0	1	1
x18	Х	Х	Х	Х	0	0	0	0	0	0	0	0	0	0	0	0	1	0	1	0	0	0	0	1	1	0	1	1	0	0	1	1
x16	Х	Х	Х	Х	0	0	0	0	0	0	0	0	0	0	0	0	1	1	1	0	0	0	0	1	1	0	1	1	0	0	1	1



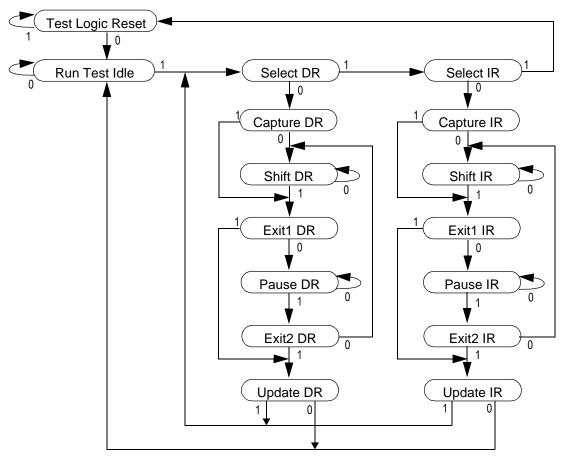
Tap Controller Instruction Set

Overview

There are two classes of instructions defined in the Standard 1149.1-1990; the standard (Public) instructions, and device specific (Private) instructions. Some Public instructions are mandatory for 1149.1 compliance. Optional Public instructions must be implemented in prescribed ways. The TAP on this device may be used to monitor all input and I/O pads, and can be used to load address, data or control signals into the RAM or to preload the I/O buffers.

When the TAP controller is placed in Capture-IR state the two least significant bits of the instruction register are loaded with 01. When the controller is moved to the Shift-IR state the Instruction Register is placed between TDI and TDO. In this state the desired instruction is serially loaded through the TDI input (while the previous contents are shifted out at TDO). For all instructions, the TAP executes newly loaded instructions only when the controller is moved to Update-IR state. The TAP instruction set for this device is listed in the following table.

JTAG Tap Controller State Diagram



Instruction Descriptions

BYPASS

When the BYPASS instruction is loaded in the Instruction Register the Bypass Register is placed between TDI and TDO. This occurs when the TAP controller is moved to the Shift-DR state. This allows the board level scan path to be shortened to facilitate testing of other devices in the scan path.



SAMPLE/PRELOAD

SAMPLE/PRELOAD is a Standard 1149.1 mandatory public instruction. When the SAMPLE / PRELOAD instruction is loaded in the Instruction Register, moving the TAP controller into the Capture-DR state loads the data in the RAMs input and I/O buffers into the Boundary Scan Register. Boundary Scan Register locations are not associated with an input or I/O pin, and are loaded with the default state identified in the Boundary Scan Chain table at the end of this section of the datasheet. Because the RAM clock is independent from the TAP Clock (TCK) it is possible for the TAP to attempt to capture the I/O ring contents while the input buffers are in transition (i.e. in a metastable state). Although allowing the TAP to sample metastable inputs will not harm the device, repeatable results cannot be expected. RAM input signals must be stabilized for long enough to meet the TAPs input data capture set-up plus hold time (tTS plus tTH). The RAMs clock inputs need not be paused for any other TAP operation except capturing the I/O ring contents into the Boundary Scan Register. Moving the controller to Shift-DR state then places the boundary scan register between the TDI and TDO pins.

EXTEST

EXTEST is an IEEE 1149.1 mandatory public instruction. It is to be executed whenever the instruction register is loaded with all logic 0s. The EXTEST command does not block or override the RAM's input pins; therefore, the RAM's internal state is still determined by its input pins.

Typically, the Boundary Scan Register is loaded with the desired pattern of data with the SAMPLE/PRELOAD command. Then the EXTEST command is used to output the Boundary Scan Register's contents, in parallel, on the RAM's data output drivers on the falling edge of TCK when the controller is in the Update-IR state.

Alternately, the Boundary Scan Register may be loaded in parallel using the EXTEST command. When the EXTEST instruction is selected, the sate of all the RAM's input and I/O pins, as well as the default values at Scan Register locations not associated with a pin, are transferred in parallel into the Boundary Scan Register on the rising edge of TCK in the Capture-DR state, the RAM's output pins drive out the value of the Boundary Scan Register location with which each output pin is associated.

IDCODE

The IDCODE instruction causes the ID ROM to be loaded into the ID register when the controller is in Capture-DR mode and places the ID register between the TDI and TDO pins in Shift-DR mode. The IDCODE instruction is the default instruction loaded in at power up and any time the controller is placed in the Test-Logic-Reset state.

SAMPLE-Z

If the SAMPLE-Z instruction is loaded in the instruction register, all RAM outputs are forced to an inactive drive state (high-Z) and the Boundary Scan Register is connected between TDI and TDO when the TAP controller is moved to the Shift-DR state.

RFU

These instructions are Reserved for Future Use. In this device they replicate the BYPASS instruction.



JTAG TAP Instruction Set Summary

Instruction	Code	Description	Notes
EXTEST	000	Places the Boundary Scan Register between TDI and TDO.	1
IDCODE	001	Preloads ID Register and places it between TDI and TDO.	1, 2
SAMPLE-Z	010	Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO. Forces all RAM output drivers to High-Z.	1
RFU	011	Do not use this instruction; Reserved for Future Use. Replicates BYPASS instruction. Places Bypass Register between TDI and TDO.	1
SAMPLE/ PRELOAD	100	Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO.	1
GSI	101	GSI private instruction.	1
RFU	110	Do not use this instruction; Reserved for Future Use. Replicates BYPASS instruction. Places Bypass Register between TDI and TDO.	1
BYPASS	111	Places Bypass Register between TDI and TDO.	1

Notes:

1. Instruction codes expressed in binary, MSB on left, LSB on right.

2. Default instruction automatically loaded at power-up and in test-logic-reset state.



JTAG Port Recommended Operating Conditions and DC Characteristics

Parameter	Symbol	Min.	Max.	Unit	Notes
3.3 V Test Port Input High Voltage	V _{IHJ3}	2.0	V _{DD3} +0.3	V	1
3.3 V Test Port Input Low Voltage	V _{ILJ3}	-0.3	0.8	V	1
2.5 V Test Port Input High Voltage	V _{IHJ2}	0.6 * V _{DD2}	V _{DD2} +0.3	V	1
2.5 V Test Port Input Low Voltage	V _{ILJ2}	-0.3	0.3 * V _{DD2}	V	1
TMS, TCK and TDI Input Leakage Current	I _{INHJ}	-300	1	uA	2
TMS, TCK and TDI Input Leakage Current	I _{INLJ}	-1	100	uA	3
TDO Output Leakage Current	I _{OLJ}	-1	1	uA	4
Test Port Output High Voltage	V _{OHJ}	1.7	_	V	5, 6
Test Port Output Low Voltage	V _{OLJ}	—	0.4	V	5, 7
Test Port Output CMOS High	V _{OHJC}	V _{DDQ} – 100 mV	_	V	5, 8
Test Port Output CMOS Low	V _{OLJC}	—	100 mV	V	5, 9

Notes:

1. Input Under/overshoot voltage must be -2 V > Vi < V_{DDn} +2 V not to exceed 4.6 V maximum, with a pulse width not to exceed 20% tTKC.

- 2. $V_{ILJ} \le V_{IN} \le V_{DDn}$
- 3. 0 V \leq V_{IN} \leq V_{ILJn}
- 4. Output Disable, $V_{OUT} = 0$ to V_{DDn}
- 5. The TDO output driver is served by the V_{DDQ} supply.
- 6. I_{OHJ} = --4 mA
- 7. I_{OLJ} = + 4 mA
- 8. I_{OHJC} = -100 uA
- 9. I_{OHJC} = +100 uA

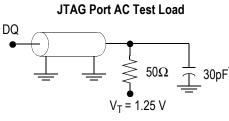
JTAG Port AC Test Conditions

Parameter	Conditions
Input high level	2.3 V
Input low level	0.2 V
Input slew rate	1 V/ns
Input reference level	1.25 V
Output reference level	1.25 V

Notes:

1. Include scope and jig capacitance.

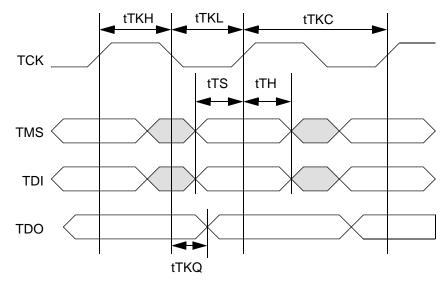
2. Test conditions as as shown unless otherwise noted.



* Distributed Test Jig Capacitance



JTAG Port Timing Diagram



JTAG Port AC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
TCK Cycle Time	tTKC	50		ns
TCK Low to TDO Valid	tTKQ		20	ns
TCK High Pulse Width	tTKH	20	_	ns
TCK Low Pulse Width	tTKL	20		ns
TDI & TMS Set Up Time	tTS	10	_	ns
TDI & TMS Hold Time	tTH	10	_	ns



GS8322Z18/36/72 Boundary Scan Chain Order

Order	x72	x36	x18		Bump	
	X12	700	XIO	x72	x36	x18
		-	TBD			

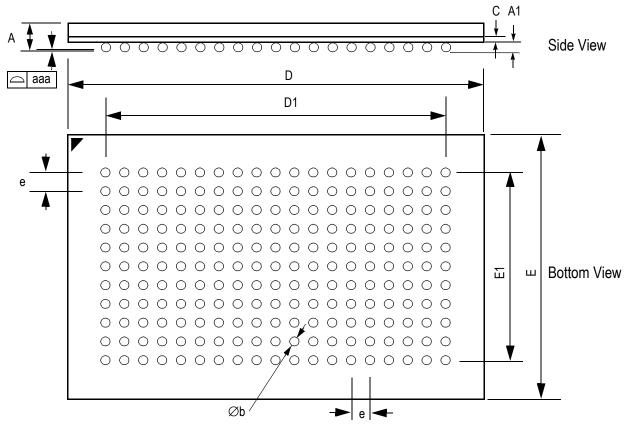
Notes:

- 1. <u>Depending</u> on the package, some input pads of the scan chain may not be connected to any external pin. In such case: <u>LBO</u> = 1, ZQ = 1, PE = 0, SD = 0, ZZ = 0, FT = 1, DP = 1, and SCD = 1.
- 2. Every DQ pad consists of two scan registers—D is for input capture, and Q is for output capture.
- 3. A single register (#194) for controlling tristate of all the DQ pins is at the end of the scan chain (i.e., the last bit shifted in this tristate control is effective after JTAG EXTEST instruction is executed.
- 4. 1 = no connect, internally set to logic value 1
- 5. 0 = no connect, internally set to logic value 0
- 6. X = no connect, value is undefined



209 BGA Package Drawing

14 mm x 22 mm Body, 1.0 mm Bump Pitch, 11 x 19 Bump Array



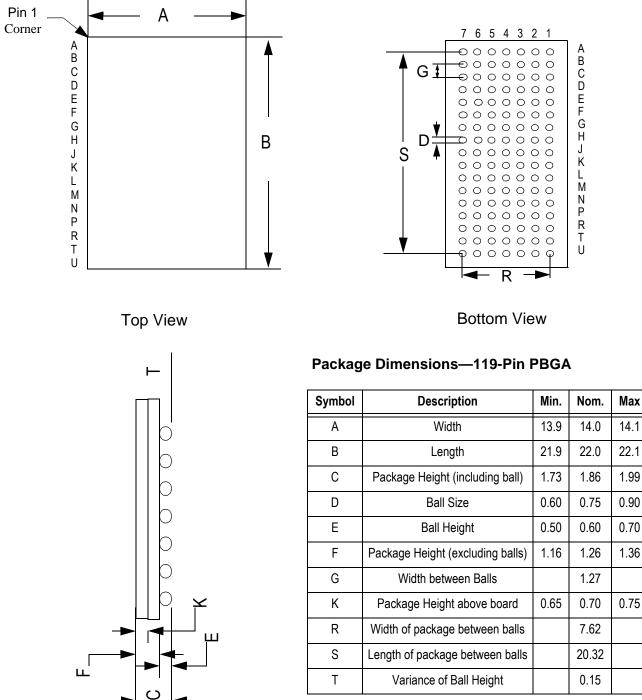
Symbol	Min	Тур	Max	Units
Α			1.70	mm
A1	0.40	0.50	0.60	mm
Øb	0.50	0.60	0.70	mm
с	0.31	0.36	0.38	mm
D	21.9	22.0	22.1	mm
D1		18.0 (BSC)		mm
E	13.9	14.0	14.1	mm
E1		10.0 (BSC)		mm
е		1.00 (BSC)		mm
aaa		0.15		mm
Rev 1.0				

 Rev: 1.00
 10/2001
 36/42

 Specifications cited are subject to change without notice. For latest documentation see http://www.gsitechnology.com.



Package Dimensions—119 Pin PBGA



Unit: mm

Side View



Ordering Information for GSI Synchronous Burst RAMs

Org	Part Number ¹	Туре	Package	Speed ² (MHz/ns)	T _A ³
2M x 18	GS8322Z18B-250	NBT Pipeline/Flow Through	119 BGA	250/6	С
2M x 18	GS8322Z18B-225	NBT Pipeline/Flow Through	119 BGA	225/6.5	С
2M x 18	GS8322Z18B-200	NBT Pipeline/Flow Through	119 BGA	200/7.5	С
2M x 18	GS8322Z18B-166	NBT Pipeline/Flow Through	119 BGA	166/8.5	С
2M x 18	GS8322Z18B-150	NBT Pipeline/Flow Through	119 BGA	150/10	С
2M x 18	GS8322Z18B-133	NBT Pipeline/Flow Through	119 BGA	133/11	С
2M x 18	GS8322Z18C-250	NBT Pipeline/Flow Through	209 BGA	250/6	С
2M x 18	GS8322Z18C-225	NBT Pipeline/Flow Through	209 BGA	225/6.5	С
2M x 18	GS8322Z18C-200	NBT Pipeline/Flow Through	209 BGA	200/7.5	С
2M x 18	GS8322Z18C-166	NBT Pipeline/Flow Through	209 BGA	166/8.5	С
2M x 18	GS8322Z18C-150	NBT Pipeline/Flow Through	209 BGA	150/10	С
2M x 18	GS8322Z18C-133	NBT Pipeline/Flow Through	209 BGA	133/11	С
1M x 36	GS8322Z36B-250	NBT Pipeline/Flow Through	119 BGA	250/6	С
1M x 36	GS8322Z36B-225	NBT Pipeline/Flow Through	119 BGA	225/6.5	С
1M x 36	GS8322Z36B-200	NBT Pipeline/Flow Through	119 BGA	200/7.5	С
1M x 36	GS8322Z36B-166	NBT Pipeline/Flow Through	119 BGA	166/8.5	С
1M x 36	GS8322Z36B-150	NBT Pipeline/Flow Through	119 BGA	150/10	С
1M x 36	GS8322Z36B-133	NBT Pipeline/Flow Through	119 BGA	133/11	С
1M x 36	GS8322Z36C-250	NBT Pipeline/Flow Through	209 BGA	250/6	С
1M x 36	GS8322Z36C-225	NBT Pipeline/Flow Through	209 BGA	225/6.5	С
1M x 36	GS8322Z36C-200	NBT Pipeline/Flow Through	209 BGA	200/7.5	С
1M x 36	GS8322Z36C-166	NBT Pipeline/Flow Through	209 BGA	166/8.5	С
1M x 36	GS8322Z36C-150	NBT Pipeline/Flow Through	209 BGA	150/10	С
1M x 36	GS8322Z36C-133	NBT Pipeline/Flow Through	209 BGA	133/11	С
512K x 72	GS8322Z72C-250	NBT Pipeline/Flow Through	209 BGA	250/6	С
512K x 72	GS8322Z72C-225	NBT Pipeline/Flow Through	209 BGA	225/6.5	С
512K x 72	GS8322Z72C-200	NBT Pipeline/Flow Through	209 BGA	200/7.5	С
512K x 72	GS8322Z72C-166	NBT Pipeline/Flow Through 209		166/8.5	С
512K x 72	GS8322Z72C-150	NBT Pipeline/Flow Through	209 BGA	150/10	С

Notes:

1. Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. Example: GS8322Z18B-150IB.

2. The speed column indicates the cycle frequency (MHz) of the device in Pipeline mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow Through mode-selectable by the user.

3. $T_A = C = Commercial Temperature Range. T_A = I = Industrial Temperature Range.$

4. GSI offers other versions this type of device in many different configurations and with a variety of different features, only some of which are covered in this data sheet. See the GSI Technology web site (<u>www.gsitechnology.com</u>) for a complete listing of current offerings.



Ordering Information for GSI Synchronous Burst RAMs (Cont.)

Org	Part Number ¹	Туре	Package	Speed ² (MHz/ns)	T _A ³
512K x 72	GS8322Z72C-133	NBT Pipeline/Flow Through	209 BGA	133/11	С
2M x 18	GS8322Z18B-250I	NBT Pipeline/Flow Through	119 BGA	250/6	I
2M x 18	GS8322Z18B-225I	NBT Pipeline/Flow Through	119 BGA	225/6.5	I
2M x 18	GS8322Z18B-200I	NBT Pipeline/Flow Through	119 BGA	200/7.5	I
2M x 18	GS8322Z18B-166I	NBT Pipeline/Flow Through	119 BGA	166/8.5	I
2M x 18	GS8322Z18B-150I	NBT Pipeline/Flow Through	119 BGA	150/10	I
2M x 18	GS8322Z18B-133I	NBT Pipeline/Flow Through	119 BGA	133/11	I
2M x 18	GS8322Z18C-250I	NBT Pipeline/Flow Through	209 BGA	250/6	I
2M x 18	GS8322Z18C-225I	NBT Pipeline/Flow Through	209 BGA	225/6.5	I
2M x 18	GS8322Z18C-200I	NBT Pipeline/Flow Through	209 BGA	200/7.5	I
2M x 18	GS8322Z18C-166I	NBT Pipeline/Flow Through	209 BGA	166/8.5	I
2M x 18	GS8322Z18C-150I	NBT Pipeline/Flow Through	209 BGA	150/10	I
2M x 18	GS8322Z18C-133I	NBT Pipeline/Flow Through	209 BGA	133/11	I
1M x 36	GS8322Z36B-250I	NBT Pipeline/Flow Through	119 BGA	250/6	I
1M x 36	GS8322Z36B-225I	NBT Pipeline/Flow Through	119 BGA	225/6.5	I
1M x 36	GS8322Z36B-200I	NBT Pipeline/Flow Through	119 BGA	200/7.5 I	
1M x 36	GS8322Z36B-166I	NBT Pipeline/Flow Through	119 BGA	166/8.5	I
1M x 36	GS8322Z36B-150I	NBT Pipeline/Flow Through	119 BGA	150/10	I
1M x 36	GS8322Z36B-133I	NBT Pipeline/Flow Through 119 BGA		133/11	I
1M x 36	GS8322Z36C-250I	NBT Pipeline/Flow Through 209 BGA		250/6	I
1M x 36	GS8322Z36C-225I	NBT Pipeline/Flow Through	209 BGA	225/6.5	I
1M x 36	GS8322Z36C-200I	NBT Pipeline/Flow Through 209 B0		200/7.5	I
1M x 36	GS8322Z36C-166I	NBT Pipeline/Flow Through 209 BGA		166/8.5	I
1M x 36	GS8322Z36C-150I	NBT Pipeline/Flow Through 209 BGA 150/		150/10	I
1M x 36	GS8322Z36C-133I	NBT Pipeline/Flow Through 209 BGA 13		133/11	I
512K x 72	GS8322Z72C-250I	NBT Pipeline/Flow Through 209 BGA		250/6	I

Notes:

1. Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. Example: GS8322Z18B-150IB.

2. The speed column indicates the cycle frequency (MHz) of the device in Pipeline mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow Through mode-selectable by the user.

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Ordering Information for GSI Synchronous Burst RAMs (Cont.)

Org	Part Number ¹	Туре	Package	Speed ² (MHz/ns)	T _A 3
512K x 72	GS8322Z72C-225I	NBT Pipeline/Flow Through	209 BGA	225/6.5	I
512K x 72	GS8322Z72C-200I	NBT Pipeline/Flow Through	209 BGA	200/7.5	I
512K x 72	GS8322Z72C-166I	NBT Pipeline/Flow Through	209 BGA	166/8.5	I
512K x 72	GS8322Z72C-150I	NBT Pipeline/Flow Through	209 BGA	150/10	I
512K x 72	GS8322Z72C-133I	NBT Pipeline/Flow Through	209 BGA	133/11	

Notes:

1. Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. Example: GS8322Z18B-150IB.

2. The speed column indicates the cycle frequency (MHz) of the device in Pipeline mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow Through mode-selectable by the user.

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36Mb Sync SRAM Datasheet Revision History

DS/DateRev. Code: Old; New	Types of Changes Format or Content	Page;Revisions;Reason
8322Z18_r1		Creation of new datasheet

